

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|---|------------------|---------|------------------|
| S1 | 1 | 10/721870 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/02 16:45 |
| S2 | 8 | ((("6313010") or ("6180493") or ("6258695") or ("5874368"))).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 11:13 |
| S3 | 1 | 10/721080 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 06:56 |
| S4 | 21053 | isolation near trench | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 09:58 |
| S5 | 392 | S4 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 09:58 |
| S6 | 248 | S5 and silicon adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 09:59 |
| S7 | 14 | S6 and (silicon adj oxide) near3 bur\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 09:59 |
| S8 | 2300 | (257/506-510).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 09:57 |
| S9 | 5403 | (438/207,218,219,294,427,221,296,353,424,221,700).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 09:58 |
| S10 | 21114 | isolation near trench | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:14 |

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| S11 | 12913 | S10 and "257"/\$.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 06:57 |
| S12 | 300 | S11 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:14 |
| S13 | 200 | S12 and silicon adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:14 |
| S14 | 50 | S13 and void | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:14 |
| S15 | 7 | S14 and (silicon adj oxide) near3 bur\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:25 |
| S16 | 1 | S15 and active near region | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:08 |
| S17 | 308960 | (isolation near trench) TI | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:49 |
| S18 | 434 | S17 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:50 |
| S19 | 271 | S18 and silicon adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:51 |
| S20 | 70 | S19 and void | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:13 |

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| S21 | 11 | S20 and (silicon adj oxide) near3 bur\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:51 |
| S22 | 4 | S21 not S15 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:16 |
| S23 | 1 | ((silicon adj oxide) near3 bur\$3) and (void with silicon adj nitride). clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 07:29 |
| S24 | 312270 | (isolation near trench) TI STI | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:12 |
| S25 | 440 | S24 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:12 |
| S26 | 276 | S25 and silicon adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:12 |
| S27 | 14 | S26 and (silicon adj oxide) near3 bur\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:51 |
| S28 | 11 | S27 and void | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:53 |
| S29 | 7 | S28 not S22 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:54 |
| S30 | 3 | S27 not S21 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/03 10:54 |

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| S31 | 2408 | (257/506-510).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 09:58 |
| S32 | 5722 | (438/207,218,219,294,427,221,296, 353,424,221,700).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 09:58 |
| S33 | 23420 | isolation near trench | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 09:58 |
| S34 | 446 | S33 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:07 |
| S35 | 16 | S34 and (silicon adj oxide) near3 bur\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:00 |
| S36 | 282 | S34 and silicon adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 09:59 |
| S37 | 16 | S36 and (silicon adj oxide) near3 bur\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:01 |
| S38 | 767 | S31 and S33 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:01 |
| S39 | 2259 | S32 and S33 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:01 |
| S40 | 5722 | (438/207,218,219,294,427,221,296, 353,424,221,700).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 10:07 |

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| S41 | 23420 | isolation near trench | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:07 |
| S42 | 2259 | S40 and S41 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:07 |
| S43 | 135 | S42 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 10:09 |
| S44 | 325828 | (isolation near trench) TI STI | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:12 |
| S45 | 499 | S44 and liner near3 silicon near nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:12 |
| S46 | 314 | S45 and silicon adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:12 |
| S47 | 83 | S46 and void | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 12:13 |
| S49 | 1 | (silicon adj nitride and lower adj inner and retract\$3 near5 (surface near3 substrate)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 13:41 |
| S50 | 1 | (silicon adj nitride and lower adj inner and retract\$3 with (surface near3 substrate)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 13:41 |

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|------------------|
| L1 | 1 | (silicon adj nitride and lower adj inner and retract\$3 near5 (surface near3 substrate)).clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 13:46 |